

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY

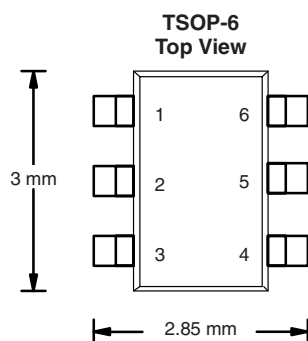
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ)
- 20	0.060 at $V_{GS} = - 4.5$ V	- 4.7	7.53 nC
	0.084 at $V_{GS} = - 2.7$ V	- 3.9	
	0.100 at $V_{GS} = - 2.5$ V	- 3.4	

FEATURES

- TrenchFET® Power MOSFET
- PWM Optimized
- 100 % R_g Tested

APPLICATIONS

- HDD
- Asynchronous Rectification
- Load Switch for Portable Devices

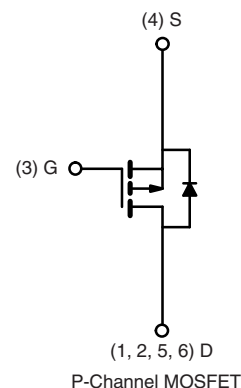

RoHS
COMPLIANT


Marking Code

AL XXX

Lot Traceability
and Date Code

Part # Code



Ordering Information: Si3443CDV-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	$T_C = 25^\circ\text{C}$	- 5.97	A
	$T_C = 70^\circ\text{C}$	- 4.6	
	$T_A = 25^\circ\text{C}$	- 4.7 ^{b, c}	
	$T_A = 70^\circ\text{C}$	- 3.4 ^{b, c}	
Pulsed Drain Current	I_{DM}	- 20	A
Continuous Source-Drain Diode Current	$T_C = 25^\circ\text{C}$	- 2.67	
	$T_A = 25^\circ\text{C}$	- 1.71 ^{b, c}	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	3.2	W
	$T_C = 70^\circ\text{C}$	2.05	
	$T_A = 25^\circ\text{C}$	2.0 ^{b, c}	
	$T_A = 70^\circ\text{C}$	1.28 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	51	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Foot (Drain)	R_{thJF}	32	39	

Notes:

a. Based on $T_C = 25^\circ\text{C}$.

b. Surface Mounted on 1" x 1" FR4 board.

c. $t = 5$ s.

d. Maximum under Steady State conditions is 110°C/W .

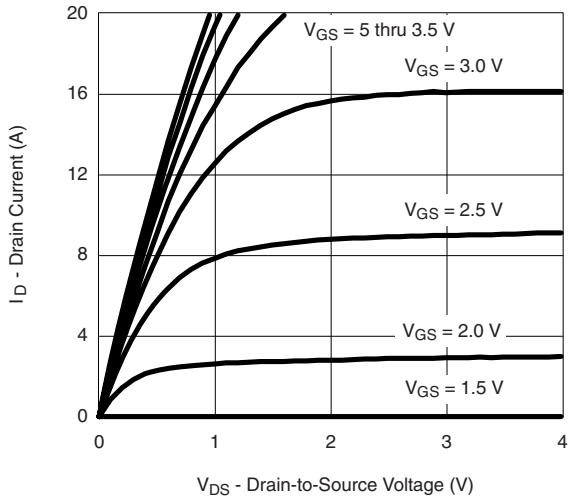
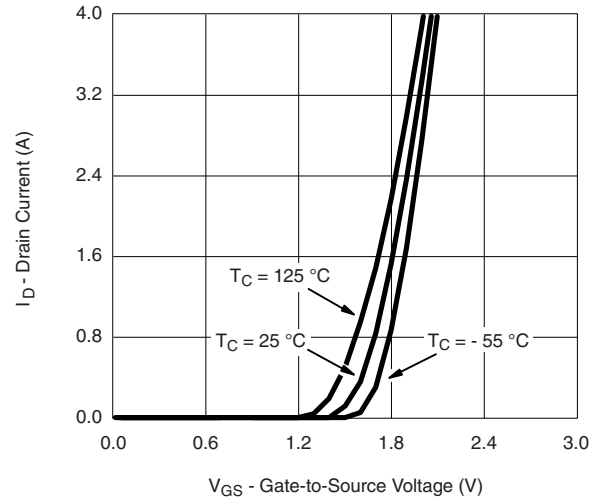
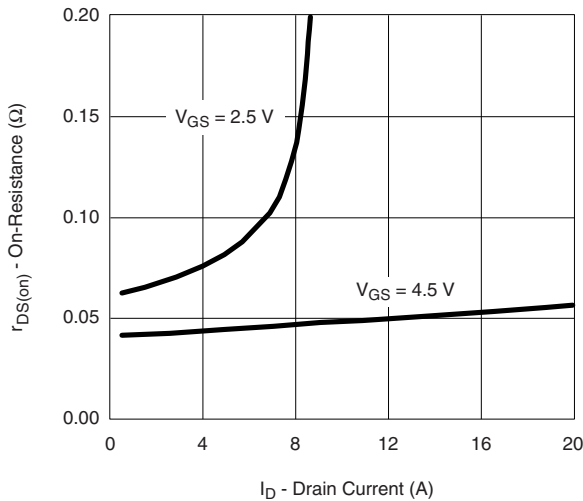
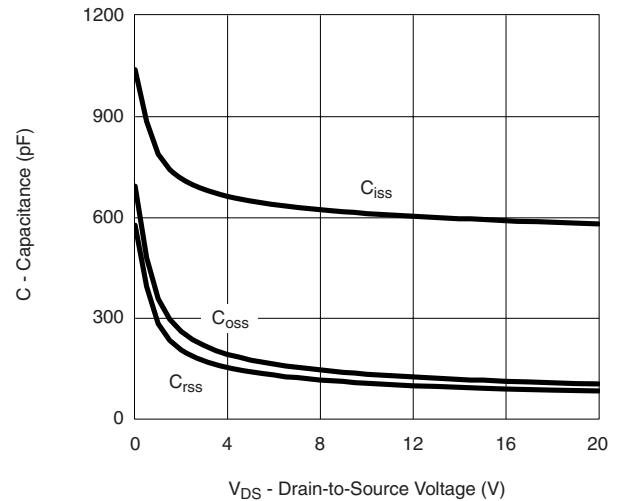
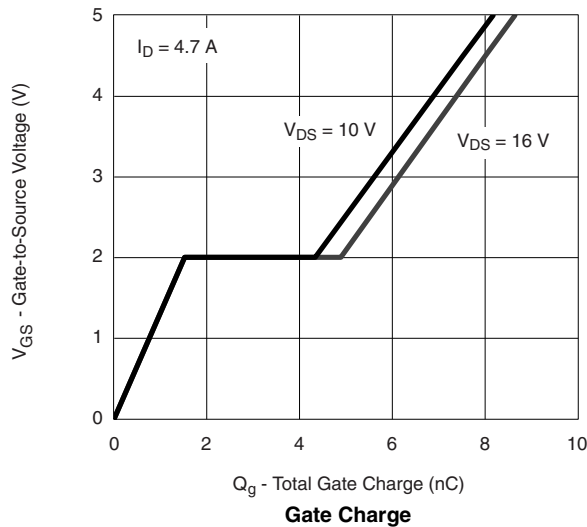
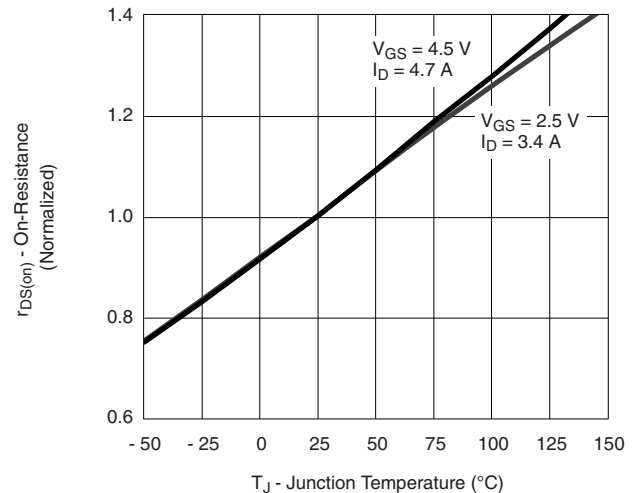
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 20			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 18.8		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			3.25		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.6		- 1.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 5 V, V _{GS} = - 4.5 V	- 20			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 4.7 A		0.050	0.060	Ω
		V _{GS} = - 2.7 V, I _D = - 3.9 A		0.0692	0.084	
		V _{GS} = - 2.5 V, I _D = - 3.4 A		0.083	0.100	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 4.7 A		15		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		610		pF
Output Capacitance	C _{oss}			132		
Reverse Transfer Capacitance	C _{rss}			105		
Total Gate Charge	Q _g	V _{DS} = - 10 V, V _{GS} = - 5.0 V, I _D = - 4.7 A		8.26	12.4	nC
				7.53	11.3	
Gate-Source Charge	Q _{gs}	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 4.7 A		1.53		
Gate-Drain Charge	Q _{gd}			2.37		
Gate Resistance	R _g	f = 1 MHz		8.5	12.75	Ω
Turn-on Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 2.12 Ω I _D ≅ - 4.7 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		27	41	ns
Rise Time	t _r			59	88.5	
Turn-Off Delay Time	t _{d(off)}			30	45	
Fall Time	t _f			11	16.5	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 2.67	A
Pulse Diode Forward Current ^a	I _{SM}				- 20	
Body Diode Voltage	V _{SD}	I _S = - 1.7 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 1.7 A, di/dt = 100 A/μs, T _J = 25 °C		20	30	ns
Body Diode Reverse Recovery Charge	Q _{rr}			9	13.5	nC
Reverse Recovery Fall Time	t _a			15		ns
Reverse Recovery Rise Time	t _b			5.1		

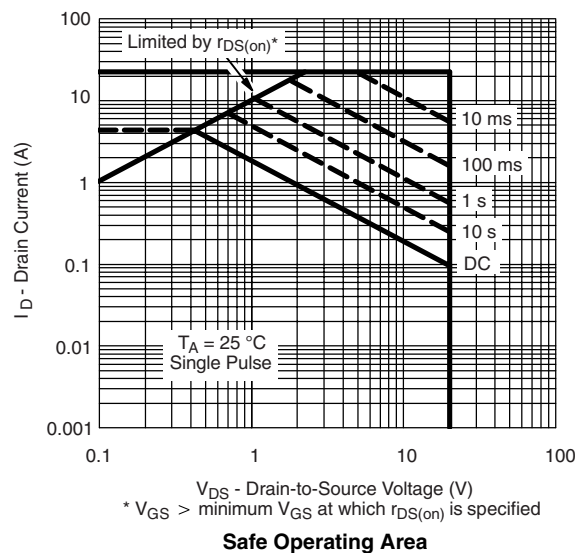
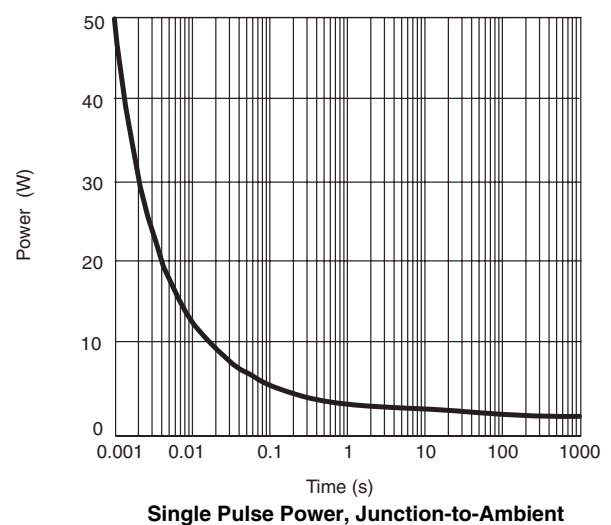
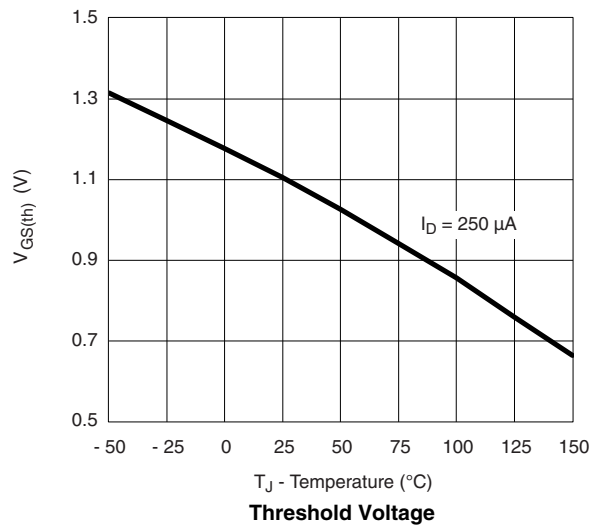
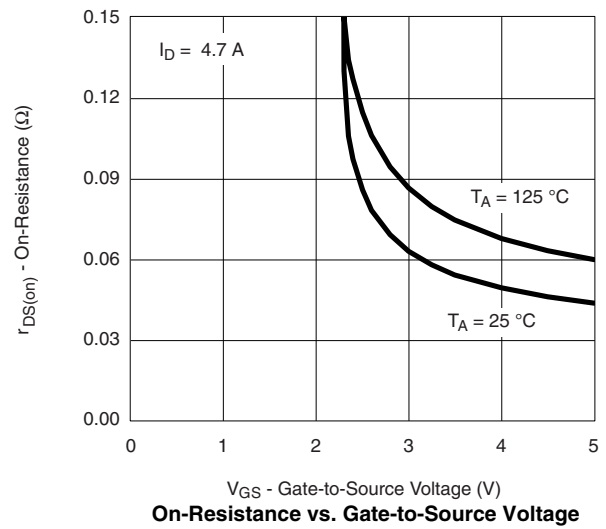
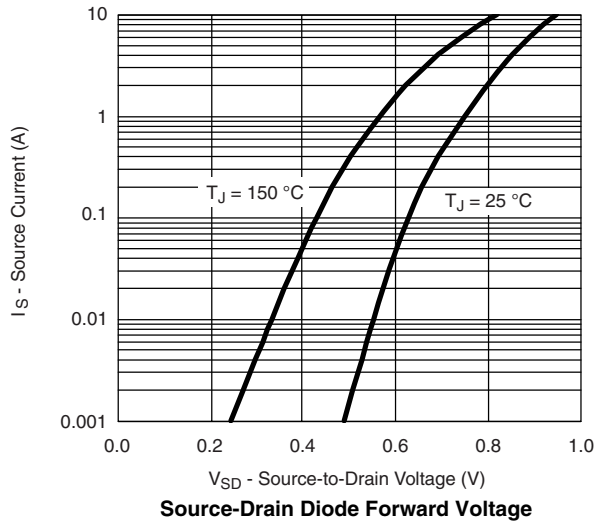
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

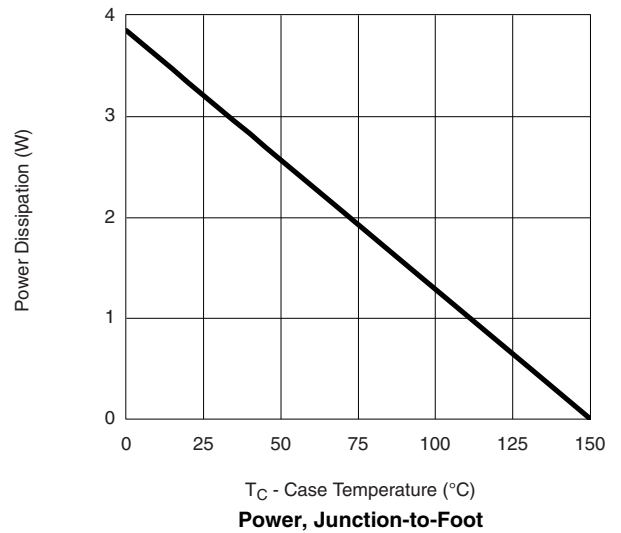
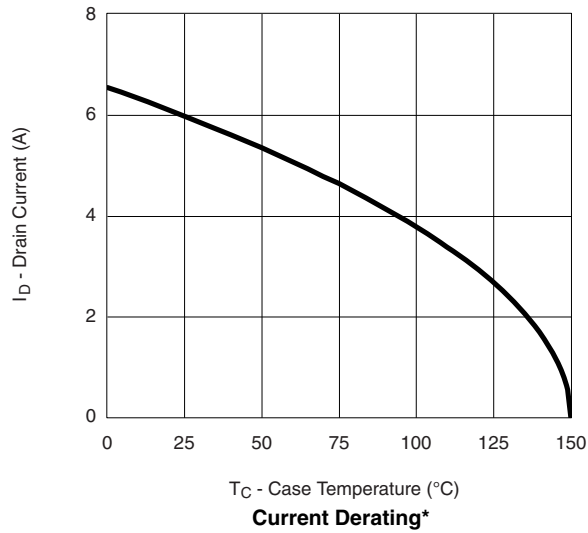
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current and Gate Voltage****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

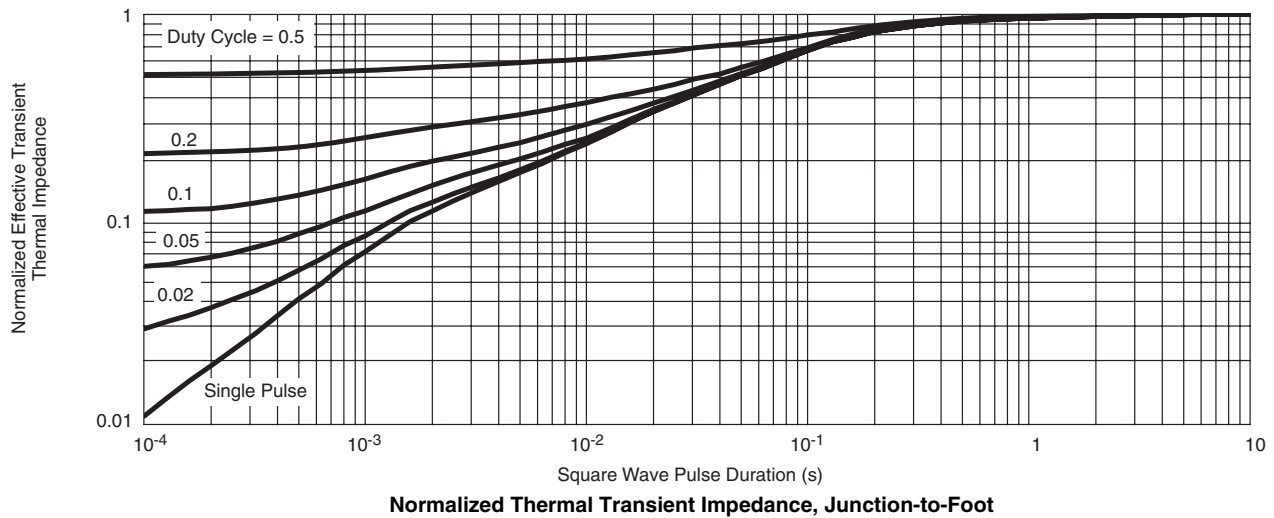
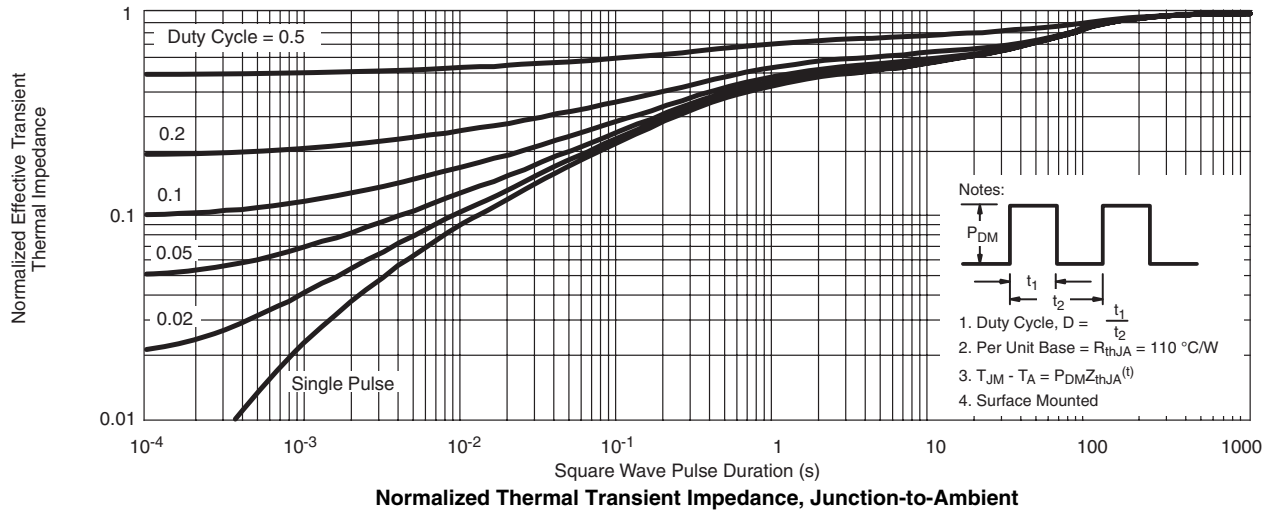
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* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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